

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device comprising:
 - a semiconductor substrate having a pattern forming region and a pattern non-forming region;
 - a wiring pattern formed on said pattern forming region;
 - a plurality of dummy patterns formed on said pattern non-forming region, said plurality of dummy patterns being formed within a plurality of dummy areas, and each of the plurality of dummy areas having a same shape; and
 - an insulating film formed on said wiring pattern and said plurality of dummy patterns; wherein said insulating film is formed by a chemical vapor deposition and is smoothed by chemical mechanical polishing;
 - wherein each of said ~~plurality of~~ dummy patterns has a plurality of parallel line patterns, ~~and each of said line patterns of said plurality of line patterns is being~~ spaced apart from each other by an area filled by the deposition of said insulating film; and
 - wherein a distance between each of said line patterns of said plurality of line patterns is less than 72 μm .
- 2-4. (Cancelled)
5. (Previously Presented) A semiconductor device according to claim 1, wherein the dummy areas each have a square shape.
6. (Previously Presented) A semiconductor device according to claim 1, wherein the dummy areas are arranged in lattice form.
7. (Cancelled)

8. (Previously Presented) A semiconductor device according to claim 1, wherein said plurality of dummy patterns are line patterns.

9. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate having a pattern area and a non-pattern area;
a conductive pattern formed on said pattern area of said semiconductor substrate; and
a plurality of dummy patterns formed on said non-pattern area of said semiconductor substrate, each of said plurality of dummy patterns having a same continuous rectangular outline shape as each other and being arranged in a matrix with predetermined spacing; and
an insulating film formed on said conductive pattern and said plurality of dummy patterns;
wherein said insulating film is formed by a chemical vapor deposition and is smoothed by chemical mechanical polishing;
wherein each of said ~~plurality of~~ dummy patterns has ~~an~~ a single square-shaped opening so that a pattern ratio of said semiconductor device is reduced; and
wherein a width of the opening of each of said ~~plurality of~~ dummy patterns is less than 72 μm .

10. (Previously Presented) A semiconductor device according to claim 9, wherein each of said plurality of dummy patterns has a square outline.

11-13. (Cancelled)

14. (Currently amended) A semiconductor device comprising:
a semiconductor substrate having a pattern area and a non-pattern area;
a conductor pattern formed on said pattern area of said semiconductor substrate;
a plurality of dummy patterns formed on said non-pattern area of said semiconductor substrate;

an insulating film formed on said conductive pattern and said plurality of dummy patterns;

wherein said insulating film is formed by a chemical vapor deposition and is smoothed by chemical mechanical polishing;

wherein each of said plurality of dummy patterns are formed in a plurality of dummy areas, each of said plurality of dummy areas having a same shape, and each of said plurality of dummy patterns being arranged in a matrix with predetermined spacing;

wherein each of said ~~plurality of~~ dummy patterns has a space portion within each of the dummy areas so that a pattern ratio of said semiconductor device is reduced; and

wherein each ~~space portion~~ of said ~~plurality of~~ dummy patterns includes an opening at the space portion, the opening having indicates a shape of a character, at least one of a letter and graphic, and each space portion opening of said ~~plurality of~~ dummy patterns has having a width less than 72 μm .

15. (Currently Amended) A semiconductor device according to claim 14, wherein each of said ~~plurality of~~ dummy patterns has a rectangular outline ~~and an opening at the space portion~~.

16. (Cancelled)

17. (Previously Presented) A semiconductor device according to claim 15, wherein the opening has a shape of a letter.

18. (Previously Presented) A semiconductor device according to claim 15, wherein the opening has a shape of a plurality of letters.

19-20. (Cancelled)

21. (Previously Presented) A semiconductor device according to claim 1, wherein said line patterns are arranged in a same direction.